



Docket No.: 91-P205-USA-G (756-151C1/CIP)
(0756-575)

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of)
Takashi INUSHIMA et al.) Group Art: 134
Serial No. 702,492)
Filed: May 20, 1990)
For: CVD APPARATUS) June 27, 1991

RECEIVED

REQUEST FOR CORRECTED RECEIPT

JUL 05 1991

Commissioner of Patents
and Trademarks
Washington, D.C. 20231

APPLICATION BRANCH

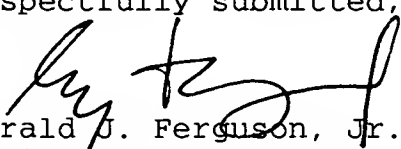
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Dear Sir: /

Attached is a copy of the Filing Receipt received from the Patent Office in the above application. The continuing data for the above-identified application is incorrect as stated on the Filing Receipt. This application is a Continuation-in-part of Serial Number 07/497,794, filed 03/22/90 as stated on page 1 of the specification, a copy of which is attached hereto. It is therefore requested that a corrected receipt be issued.

Respectfully submitted,

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CONF. mailed 5-6-91
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CONFIRMATION OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage on First Class Mail in an envelope addressed to: Commissioner of Patents and Trademarks, Washington, D.C. 20530, on 6/27/91.


Cecilia J. Campbell

CVD APPARATUS

Related Applications

This Application is a Continuation-in-Part of copending Application Serial No. 07/497,794; which in turn is a Continuation of Application Serial No. 07/091,770, now abandoned.

Background of the Invention

The invention relates to a photo enhanced CVD apparatus.

Many chemical vapor deposition (CVD) processes are used, such as APCVD, LP CVD, plasma CVD, thermal CVD and so forth, for depositing a film on a substrate. While these processes have their own peculiar characteristics respectively, the temperature at which each process is carried out is commonly rather high. Such high temperature process is not suitable for formation of passivation film on an aluminum electrode arrangement.

Photo enhanced CVD process has attracted the interest of artisans because it can be carried out at a comparatively low temperature. This process is based on the energy of light, namely an optical reaction is carried out. For example, in the case of photo CVD process using silane and ammonia, mercury atoms are excited by irradiation of ultraviolet light of 2,537Å in wavelength. The process is carried out to deposit a silicon nitride film on a substrate in accordance with the following equation:

FILING RECEIPT



UNITED STATES DEPARTMENT OF COMMERCE
Patent and Trademark Office
ASSISTANT SECRETARY AND COMMISSIONER
OF PATENTS AND TRADE MARKS
Washington, D.C. 20231

0756-575

SERIAL NUMBER	FILING DATE	GRP ART UNIT	FIL FEE REC'D	ATTORNEY DOCKET NO.	ORWGS	TOT CL	IND CL
07/702,492	05/20/1991	134	\$ 630.00	91-P205-USA-H	8	6	1

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Receipt is acknowledged of the patent application identified herein. It will be considered in its order and you will be notified as to the examination thereof. Be sure to give the U.S. SERIAL NUMBER, DATE OF FILING, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this transmittal.

Applicant(s)

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CONTINUING DATA AS CLAIMED BY APPLICANT-

THIS APPLN IS A DIV OF 07/497,794 03/22/90
WHICH IS A CON OF 07/091,770 09/01/87

ABAN

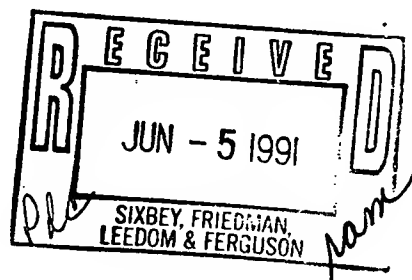
FOREIGN/PCT APPLICATIONS-JAPAN
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61-213323
61-213324
61-213325
62-141050

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TITLE
CVD APPARATUS

PRELIMINARY CLASS: 118



(see reverse)